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## NTE92 (NPN) & NTE93 (PNP) Silicon Complementary Transistors Hi-Fi Power Amp, Audio Output

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector-Base Voltage, $V_{CBO}$ .....	200V
Collector-Emitter Voltage, $V_{CEO}$ .....	200V
Emitter-Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$ .....	15A
Base Current, $I_B$ .....	5A
Collector Power Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_C$ .....	150W
Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +150°C

Note 1. Matched complementary pairs are available upon request (NTE93MCP). Matched complementary pairs have their gain specification ( $h_{FE}$ ) matched to within 10% of each other.

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 200V$	-	-	0.1	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{BE} = 6V$	-	-	0.1	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50mA$	200	-	-	V
DC Current Gain	$h_{FE}$	$V_{CE} = 4V, I_C = 5A$	30	120	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10A, I_B = 1A$	-	3	-	V
Transistion Frequency	$f_T$	$V_{CE} = 12V, I_E = 0.5A$	-	20	-	MHz

